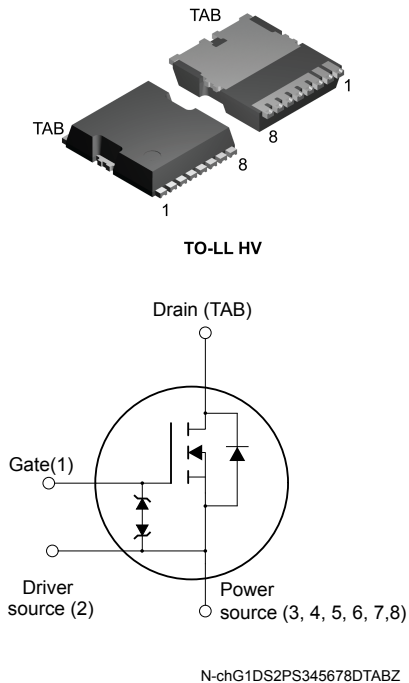


N-channel 600 V, 105 mΩ typ., 25 A, MDmesh™ M6 Power MOSFET in a TO-LL HV package



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STO33N60M6	600 V	125 mΩ	25 A

- Reduced switching losses
- Lower R_{DS(on)} per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected
- High creepage package
- Excellent switching performance thanks to the extra driving source pin

Applications

- Switching applications
- LLC converters
- Boost PFC converters

Description

The new MDmesh™ M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent R_{DS(on)} per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

Product status link	
STO33N60M6	
Product summary	
Order code	STO33N60M6
Marking	33N60M6
Package	TO-LL HV
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ }^{\circ}\text{C}$	25	A
	Drain current (continuous) at $T_{case} = 100\text{ }^{\circ}\text{C}$	15.8	
$I_D^{(1)}$	Drain current (pulsed)	78	A
P_{TOT}	Total dissipation at $T_{case} = 25\text{ }^{\circ}\text{C}$	230	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 25\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.54	$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb	46	$^{\circ}\text{C}/\text{W}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_{Jmax})	4	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	500	mJ

2 Electrical characteristics

($T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{DSS}}$	Drain-source breakdown voltage	$V_{\text{GS}} = 0\text{ V}$, $I_{\text{D}} = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current	$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$			1	μA
		$V_{\text{GS}} = 0\text{ V}$, $V_{\text{DS}} = 600\text{ V}$, $T_{\text{case}} = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{\text{DS}} = 0\text{ V}$, $V_{\text{GS}} = \pm 25\text{ V}$			± 5	μA
$V_{\text{GS(th)}}$	Gate threshold voltage	$V_{\text{DS}} = V_{\text{GS}}$, $I_{\text{D}} = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{\text{DS(on)}}$	Static drain-source on-resistance	$V_{\text{GS}} = 10\text{ V}$, $I_{\text{D}} = 12.5\text{ A}$		105	125	$\text{m}\Omega$

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{\text{DS}} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{\text{GS}} = 0\text{ V}$	-	1515	-	pF
C_{oss}	Output capacitance		-	128	-	
C_{rss}	Reverse transfer capacitance		-	4.2	-	
$C_{\text{oss eq.}}^{(1)}$	Equivalent output capacitance	$V_{\text{DS}} = 0\text{ to }480\text{ V}$, $V_{\text{GS}} = 0\text{ V}$	-	269	-	pF
R_{G}	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_{\text{D}} = 0\text{ A}$	-	1.5	-	Ω
Q_{g}	Total gate charge	$V_{\text{DD}} = 480\text{ V}$, $I_{\text{D}} = 25\text{ A}$, $V_{\text{GS}} = 0\text{ to }10\text{ V}$ (see Figure 14. Gate charge test circuit)	-	33.4	-	nC
Q_{gs}	Gate-source charge		-	7.2	-	
Q_{gd}	Gate-drain charge		-	16.3	-	

1. $C_{\text{oss eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{\text{d(on)}}$	Turn-on delay time	$V_{\text{DD}} = 300\text{ V}$, $I_{\text{D}} = 12.5\text{ A}$, $R_{\text{G}} = 4.7\text{ }\Omega$, $V_{\text{GS}} = 10\text{ V}$ (see Figure 13. Switching times test circuit for resistive load and Figure 18. Switching time waveform)	-	19.5	-	ns
t_{r}	Rise time		-	33	-	
$t_{\text{d(off)}}$	Turn-off delay time		-	38.5	-	
t_{f}	Fall time		-	7.5	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		25	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		78	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 25\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	265		ns
Q_{rr}	Reverse recovery charge		-	3.07		μC
I_{RRM}	Reverse recovery current		-	23.2		A
t_{rr}	Reverse recovery time	$I_{SD} = 25\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	374		ns
Q_{rr}	Reverse recovery charge		-	5.78		μC
I_{RRM}	Reverse recovery current		-	30.9		A

1. Pulse width is limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

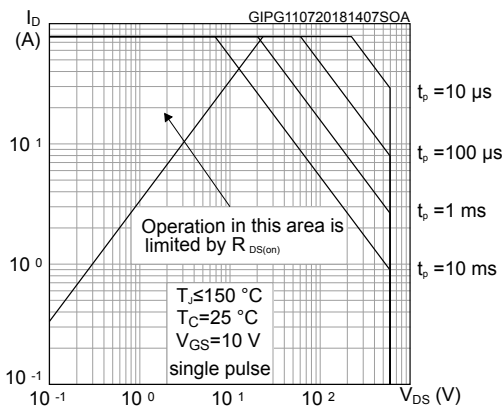


Figure 2. Thermal impedance

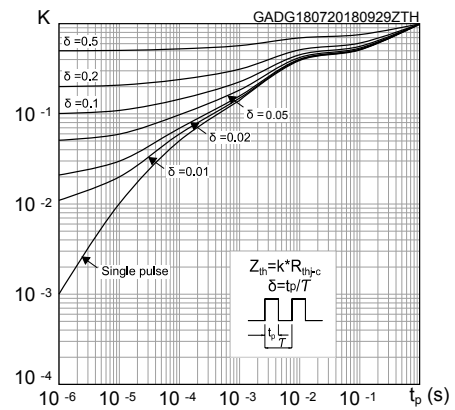


Figure 3. Output characteristics

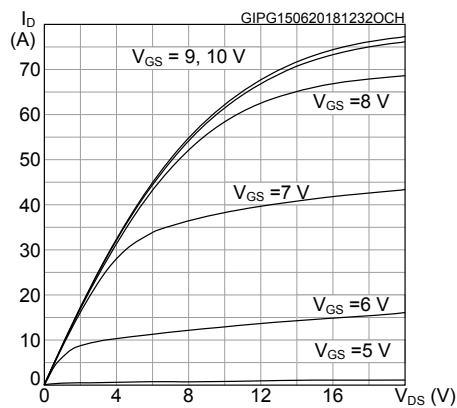


Figure 4. Transfer characteristics

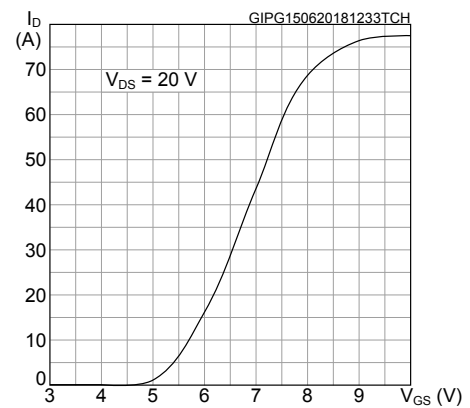


Figure 5. Gate charge vs gate-source voltage

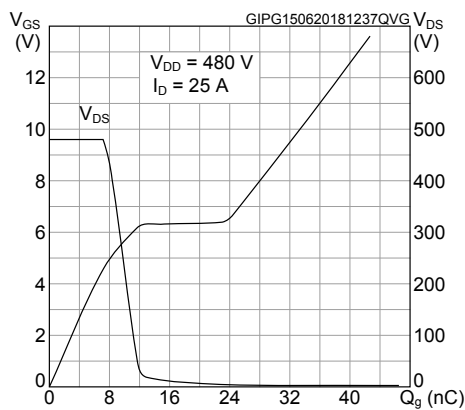


Figure 6. Static drain-source on-resistance

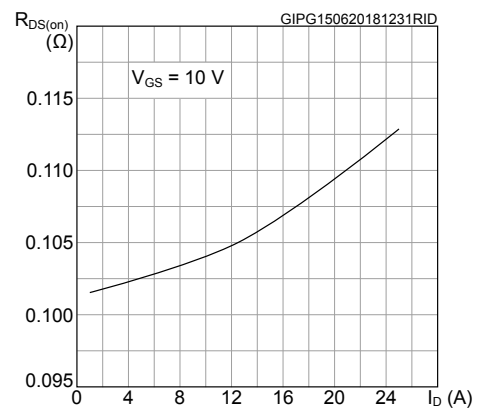


Figure 7. Capacitance variations

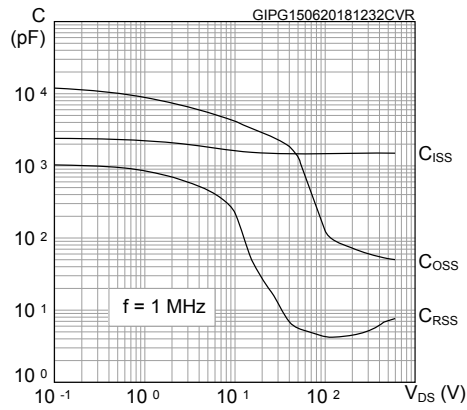


Figure 8. Normalized gate threshold voltage vs temperature

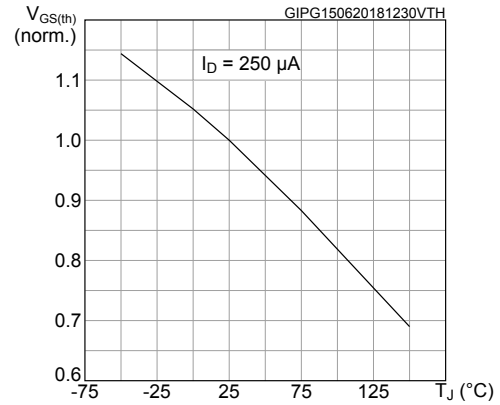


Figure 9. Normalized on-resistance vs temperature

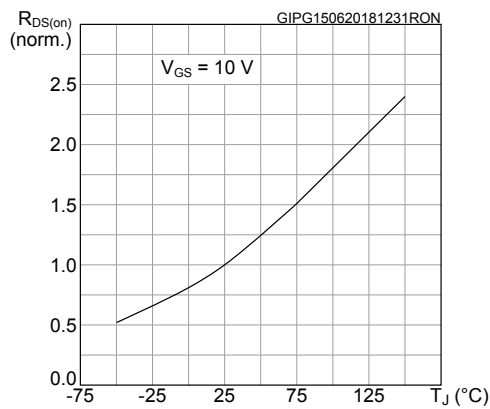


Figure 10. Normalized $V_{(BR)DSS}$ vs temperature

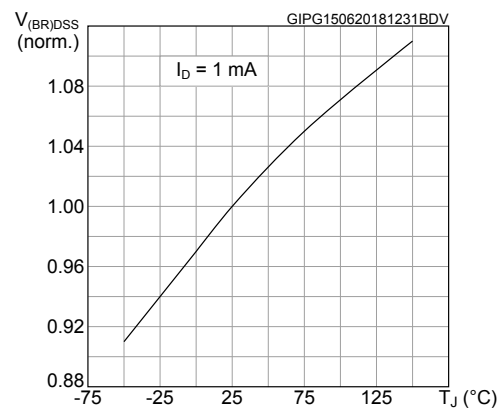


Figure 11. Output capacitance stored energy

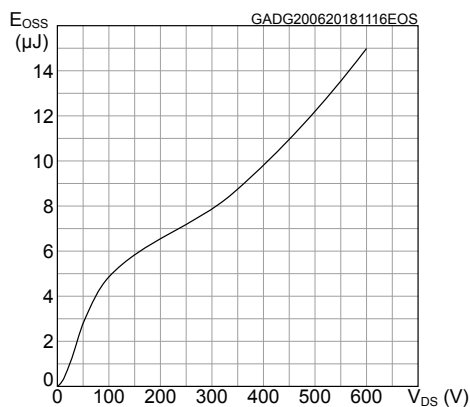
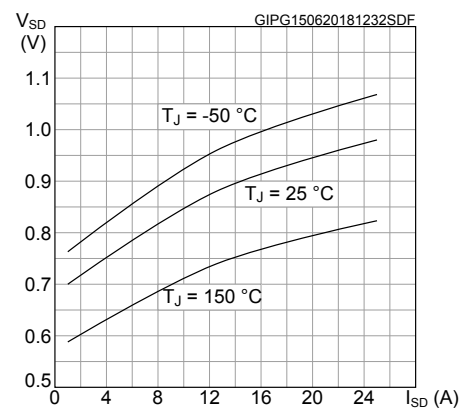
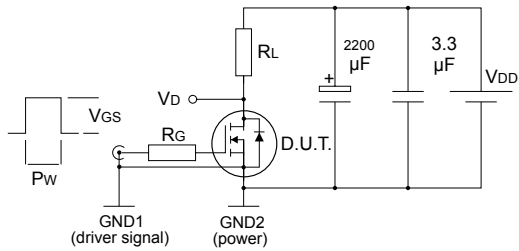


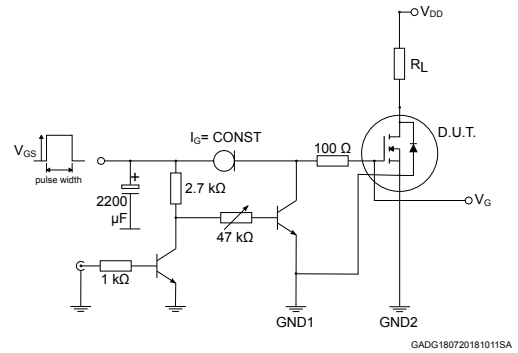
Figure 12. Source-drain diode forward characteristics



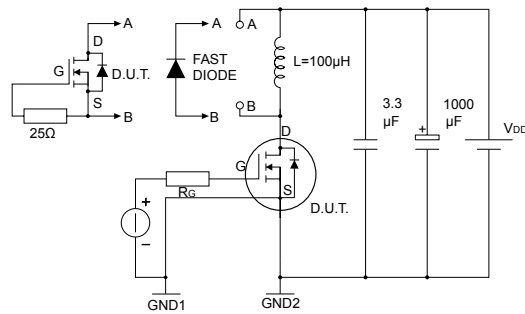
3 Test circuits

Figure 13. Switching times test circuit for resistive load


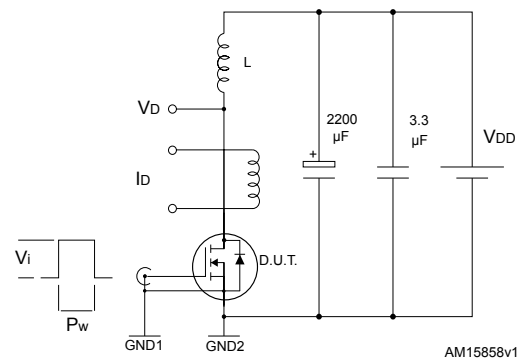
AM15855v1

Figure 14. Gate charge test circuit


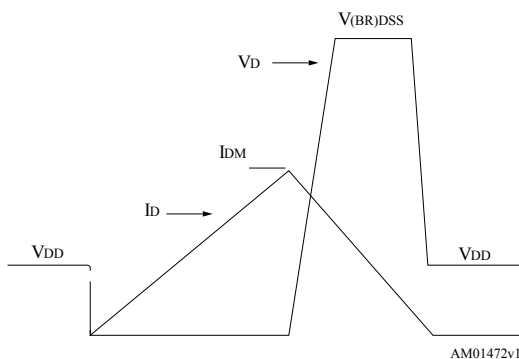
GADG180720181011SA

Figure 15. Test circuit for inductive load switching and diode recovery times


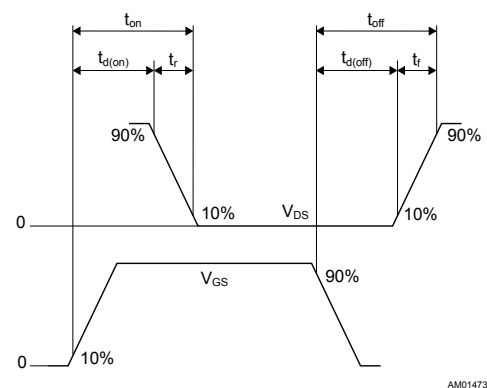
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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


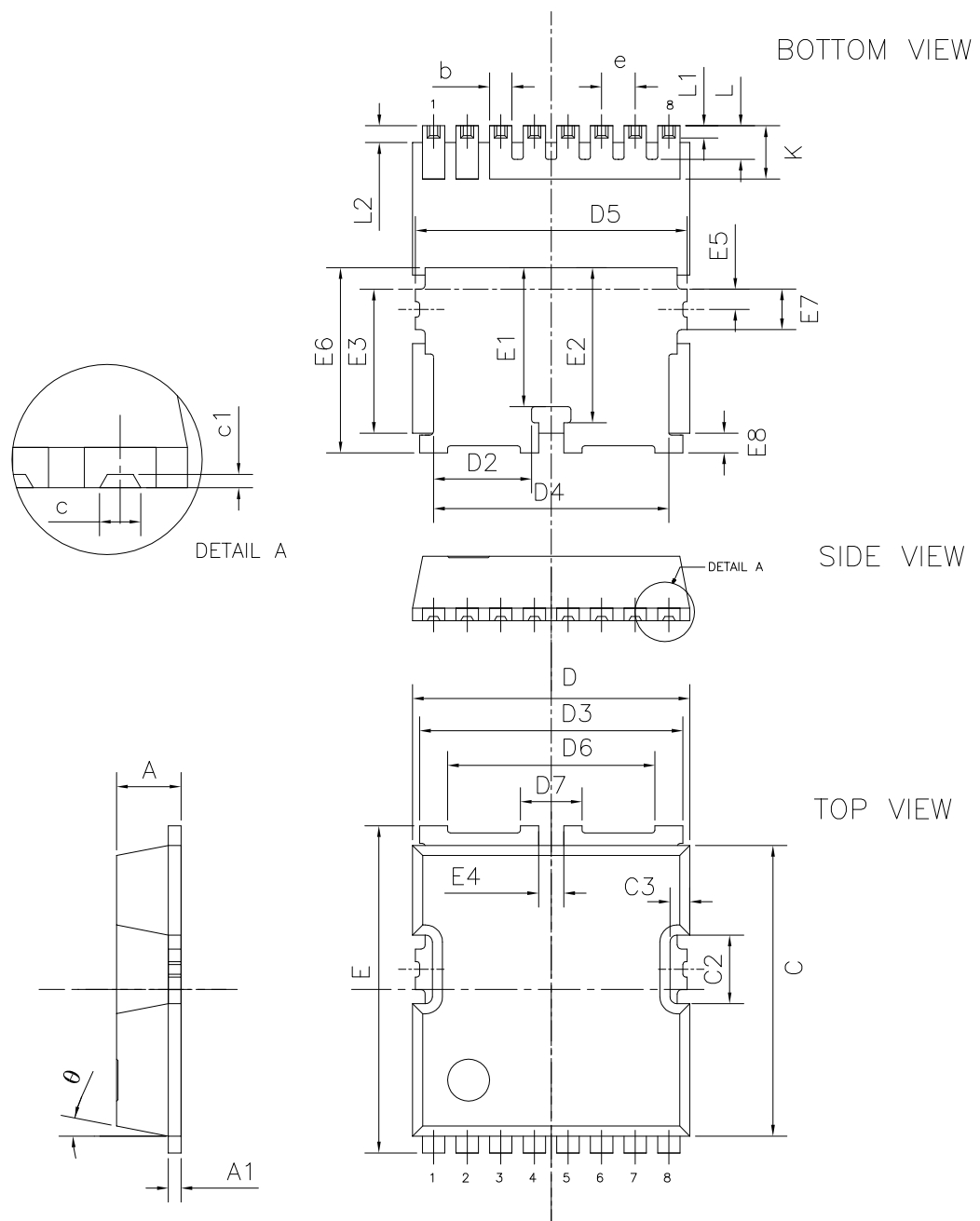
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-LL HV package information

Figure 19. TO-LL HV package outline

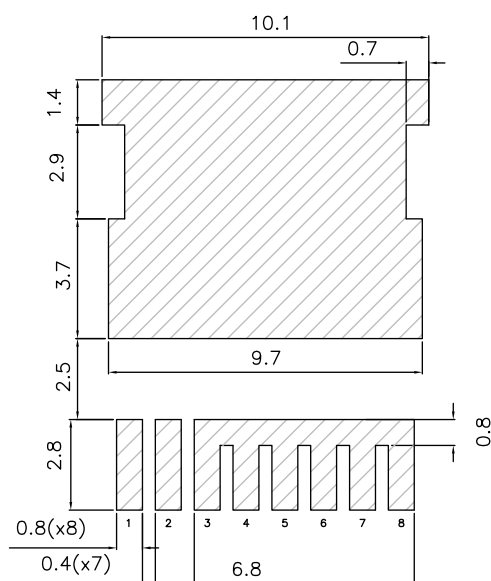


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Table 8. TO-LL HV package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.40
A1	0.40	0.48	0.60
b		0.80	0.93
c		0.46	
c1		0.15	
C	10.28	10.38	10.48
C2	2.35	2.45	2.55
C3		0.71	
D	9.80	9.90	10.00
D2	3.30	3.50	3.70
D3	9.30	9.40	9.50
D4	8.20	8.40	8.60
D5	9.50	9.70	9.90
D6		7.40	
D7		2.20	
e		1.20	
E	11.48	11.68	11.88
E1		4.96	
E2		5.54	
E3		5.14	
E4		0.90	
E5		0.72	
E6	6.41	6.61	6.81
E7	0.50	0.70	0.90
K	1.70	1.90	2.10
L	1.05	1.20	1.35
L1	0.25	0.35	0.45
L2	0.40	0.60	0.80
θ		11°	

Figure 20. TO-LL HV recommended footprint (dimensions are in mm)



DM00276569_1

Revision history

Table 9. Document revision history

Date	Version	Changes
11-Jul-2018	1	Initial release.

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